

ABSTRACT

A substrate processing method comprises providing a substrate 105 comprising etch resistant material 210 in a process zone 155, such as an energized gas zone in a process chamber 110. The etch resistant material 210 may comprise a resist material 230 over mask material 240. The process may further comprise removing the etch resistant material 210, such as the resist material 230, in the process zone 155 before etching underlying layers.

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